

Rev.E Mar.-2016

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

$V_{CE(sat)}$, 2SA719
 Low $V_{CE(sat)}$, complementary pair with 2SA719.

Audio frequency power amplifier and driver.

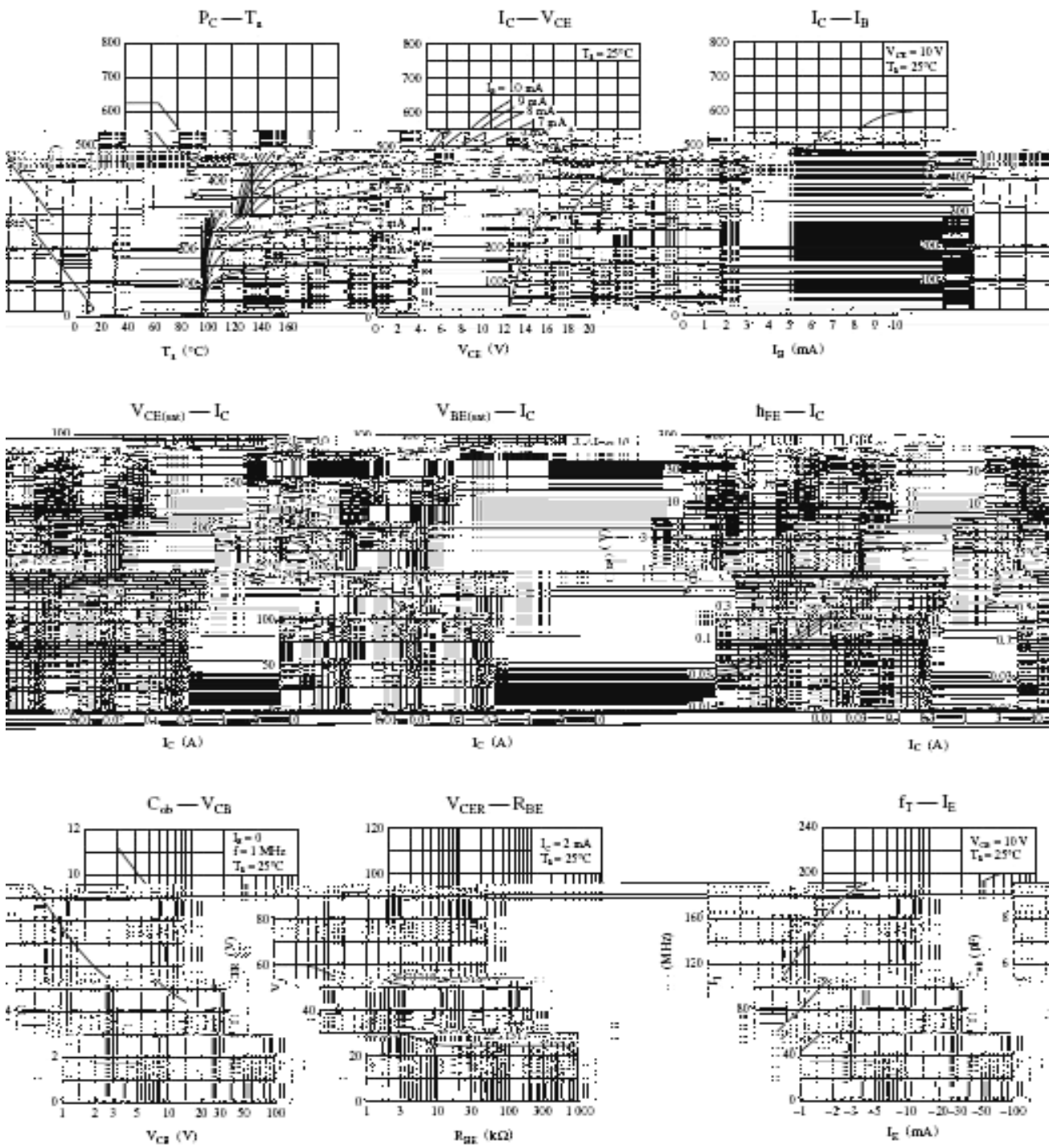


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	85~170	120~240	170~340

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	500	mA
Collector Current – Continuous(Pulse)	I_{CP}	1.0	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	7.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=20V$ $I_E=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=10V$ $I_C=150mA$	85	160	340	
	$h_{FE(2)}$	$V_{CE}=10V$ $I_C=500mA$	40	90		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=300mA$ $I_B=30mA$		0.35	0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=300mA$ $I_B=30mA$		1.1	1.5	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		6.0	15	pF





BR:

C1317

Q: h_{FE}

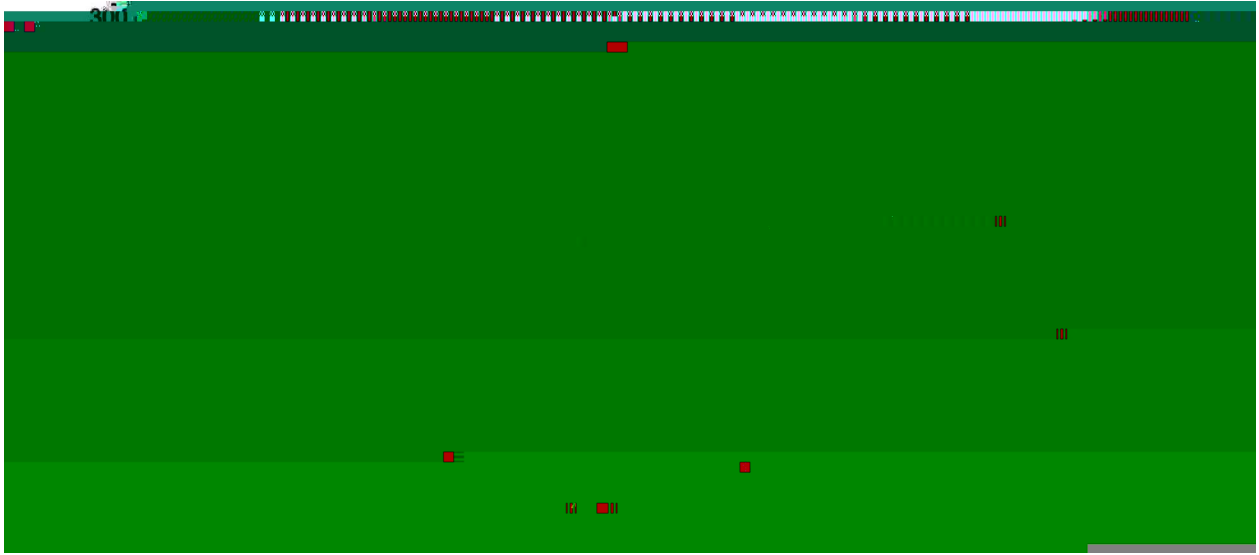
Note:

BR: Company Code.

C1317: Product Type.

Q: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.



1	25	150	60	90sec;	Note:	1.Preheating:25~150 , Time:60~90sec.
2	255±5		5±0.5sec;		2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.	

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)
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